NTD3055L104

Advance Information

Power MOSFET
12 Amps, 60 Volts, Logic Level
N–Channel DPAK

Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

Features

- Lower $R_{DS(on)}$
- Lower $V_{DS(on)}$
- Tighter V_{SD} Specification
- Lower Diode Reverse Recovery Time
- Lower Reverse Recovery Stored Charge

Typical Applications

- Power Supplies
- Converters
- Power Motor Controls
- Bridge Circuits

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain–to–Source Voltage	V_{DSS}	60	Vdc
Drain–to–Gate Voltage (R_{GS} = 10 MΩ)	V_{DGR}	60	Vdc
Gate–to–Source Voltage – Continuous – Non–Repetitive ($t_p \le 10$ ms)	 V_{GS} V_{GS}	 ±15 ±20	Vdc
Drain Current – Continuous @ T_A = 25°C – Continuous @ T_A = 100°C – Single Pulse ($t_p \le 10$ μs)	 I_D I_D I_{DM}	 12 10 45	 Adc Apk
Total Power Dissipation @ T_A = 25°C Derate above 25°C Total Power Dissipation @ T_A = 25°C (Note 1.) Total Power Dissipation @ T_A = 25°C (Note 2.)	P_D	48 0.32 2.1 1.5	W W/°C W W
Operating and Storage Temperature Range	T_J, T_{stg}	–55 to +175	°C
Single Pulse Drain–to–Source Avalanche Energy – Starting T_J = 25°C (V_{DD} = 25 Vdc, V_{GS} = 5.0 Vdc, L = 1.0 mH $I_{L(pk)}$ = 11 A, V_{DS} = 60 Vdc)	E_{AS}	61	mJ
Thermal Resistance – Junction–to–Case – Junction–to–Ambient (Note 1.) – Junction–to–Ambient (Note 2.)	 $R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JA}$	 3.13 71.4 100	 °C/W
Maximum Lead Temperature for Soldering Purposes, 1/8″ from case for 10 seconds	T_L	260	°C

1. When surface mounted to an FR4 board using 1″ pad size, (Cu Area 1.127 in^2).
2. When surface mounted to an FR4 board using the minimum recommended pad size, (Cu Area 0.412 in^2).

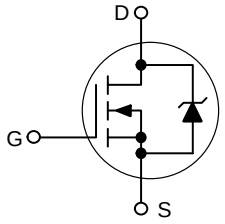
This document contains information on a new product. Specifications and information herein are subject to change without notice.

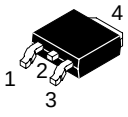
ON Semiconductor

http://onsemi.com

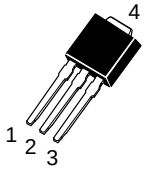
12 AMPERES
60 VOLTS
$R_{DS(on)}$ = 104 mΩ

N–Channel





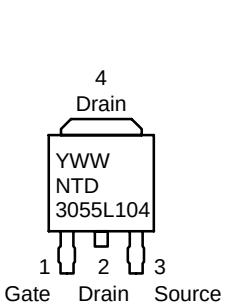
CASE 369A
DPAK
(Bent Lead)
STYLE 2

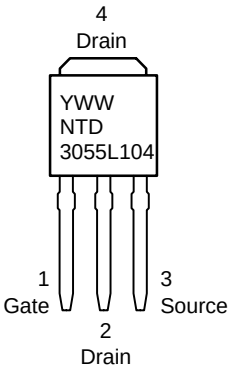


CASE 369
DPAK
(Straight Lead)
STYLE 2

NTD3055L104 = Device Code
Y = Year
WW = Work Week

MARKING DIAGRAMS & PIN ASSIGNMENTS





ORDERING INFORMATION

Device	Package	Shipping
NTD3055L104	DPAK	75 Units/Rail
NTD3055L104–1	DPAK Straight Lead	75 Units/Rail
NTD3055L104T4	DPAK	2500 Tape & Reel

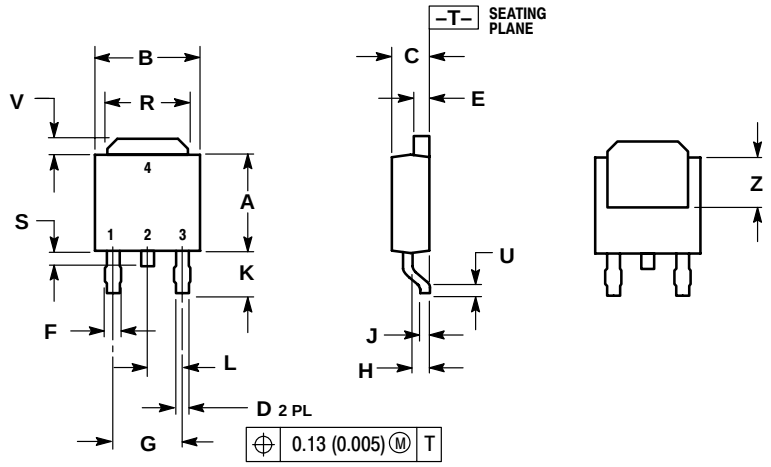
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain–to–Source Breakdown Voltage (Note 3.) (V_{GS} = 0 Vdc, I_D = 250 μAdc) Temperature Coefficient (Positive)		$V_{(BR)DSS}$	 60 –	 70 62.9	 – –	Vdc mV/°C
Zero Gate Voltage Drain Current (V_{DS} = 60 Vdc, V_{GS} = 0 Vdc) (V_{DS} = 60 Vdc, V_{GS} = 0 Vdc, T_J = 150°C)		I_{DSS}	 – –	 – –	 1.0 10	μAdc
Gate–Body Leakage Current (V_{GS} = ±15 Vdc, V_{DS} = 0 Vdc)		I_{GSS}	–	–	±100	nAdc
ON CHARACTERISTICS (Note 3.)						
Gate Threshold Voltage (Note 3.) (V_{DS} = V_{GS}, I_D = 250 μAdc) Threshold Temperature Coefficient (Negative)		$V_{GS(th)}$	 1.0 –	 1.6 4.2	 2.0 –	Vdc mV/°C
Static Drain–to–Source On–Resistance (Note 3.) (V_{GS} = 5.0 Vdc, I_D = 6.0 Adc)		$R_{DS(on)}$	 –	 89	 104	mOhm
Static Drain–to–Source On–Voltage (Note 3.) (V_{GS} = 5.0 Vdc, I_D = 12 Adc) (V_{GS} = 5.0 Vdc, I_D = 6.0 Adc, T_J = 150°C)		$V_{DS(on)}$	 – –	 0.98 0.86	 1.50 –	Vdc
Forward Transconductance (Note 3.) (V_{DS} = 8.0 Vdc, I_D = 6.0 Adc)		g_{FS}	–	9.1	–	mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = 25 Vdc, V_{GS} = 0 Vdc, f = 1.0 MHz)	C_{iss}	–	316	440	pF
Output Capacitance		C_{oss}	–	105	150	
Transfer Capacitance		C_{rss}	–	35	70	
SWITCHING CHARACTERISTICS (Note 4.)						
Turn–On Delay Time	(V_{DD} = 30 Vdc, I_D = 12 Adc, V_{GS} = 5.0 Vdc, R_G = 9.1 Ω) (Note 3.)	$t_{d(on)}$	–	9.2	20	ns
Rise Time		t_r	–	104	210	
Turn–Off Delay Time		$t_{d(off)}$	–	19	40	
Fall Time		t_f	–	40.5	80	
Gate Charge	(V_{DS} = 48 Vdc, I_D = 12 Adc, V_{GS} = 5.0 Vdc) (Note 3.)	Q_T	–	7.4	20	nC
		Q_1	–	2.0	–	
		Q_2	–	4.0	–	
SOURCE–DRAIN DIODE CHARACTERISTICS						
Forward On–Voltage	(I_S = 12 Adc, V_{GS} = 0 Vdc) (Note 3.) (I_S = 12 Adc, V_{GS} = 0 Vdc, T_J = 150°C)	V_{SD}	 – –	 0.95 0.82	 1.2 –	Vdc
Reverse Recovery Time	(I_S = 12 Adc, V_{GS} = 0 Vdc, dI_S/dt = 100 A/μs) (Note 3.)	t_{rr}	–	35	–	ns
		t_a	–	21	–	
		t_b	–	14	–	
Reverse Recovery Stored Charge		Q_{RR}	–	0.04	–	μC

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

PACKAGE DIMENSIONS

DPAK
CASE 369A–13
ISSUE AA

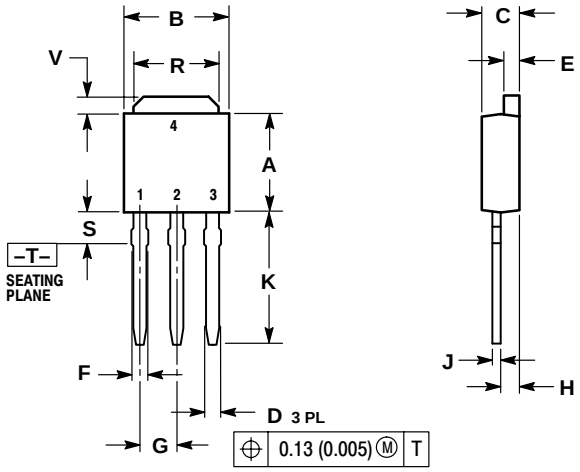


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.175	0.215	4.45	5.46
S	0.020	0.050	0.51	1.27
U	0.020	---	0.51	---
V	0.030	0.050	0.77	1.27
Z	0.138	---	3.51	---

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

DPAK
CASE 369–07
ISSUE M



NOTES:
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	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1.27

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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